Transmittal Letter filed herewith. A clean copy of the claims as amended is appended hereto.

Kindly enter the following amendments:

IN THE CLAIMS:

Please amend Claims 1, 8, and 30 as follows:

A1

1. (Five Times Amended) A method for forming a semiconductor device having a laminated structure including a dielectric film made from a metal oxide formed on a surface of a heated substrate and a CVD high melting point metal nitride film, wherein said metal nitride film is directly formed on said dielectric film by introducing a source gas containing said high melting point metal into a chamber in which said substrate is contained,

said method comprising a step of heating said substrate in [an] a non-reactive ambient [that is non-reactive with respect to] having no component that reacts with said metal oxide formed on said surface of said substrate in said chamber, wherein said non-reactive ambient includes [at least one] a member of the group consisting of a gas non-reactive with respect to said metal oxide contained in said dielectric film and NH_3 gas, and

introducing into said chamber a source gas for forming said CVD-TiN film and NH_3 gas, following said heating step, and further

wherein a temperature of said substrate is set at a prescribed temperature, before said source gas containing said high melting point metal is introduced into said chamber.

h2 8. (Four Times Amended) A method for forming a semiconductor device having a laminated structure of a dielectric made from a metal oxide and a CVD high melting point metal nitride film formed thereover, wherein said metal nitride film is directly formed on said dielectric film by introducing a source gas containing said high melting point metal into a chamber in which said dielectric film is contained, said method comprising;

heating a substrate onto which said dielectric film is formed to a prescribed temperature in an ambient [having a] comprising NH_3 [atmosphere of] gas at a partial pressure no greater [partial pressure] than 1.0 Torr and no less than 0.1 Torr before the introduction of said source gas containing said high melting point metal, wherein said NH_3 gas does not react with said dielectric film.

h3 30. (Once Amended) A method for forming a CVD-TiN film, wherein a titanium nitride (TiN) film is formed on a dielectric film that includes an oxide material formed by a CVD film forming process within a CVD film forming device, said method comprising:

heating a substrate provided with said dielectric film in said CVD film forming device, within an atmosphere [with a non-reactive gas with respect to] having no component which reacts with said dielectric film including said oxide material; and

forming said titanium nitride (TiN) film on said dielectric film in said CVD film forming device.